3.3 V/5 V ECL 4-Input OR/NOR

MC10EP01, MC100EP01

Description

The MC10EP01 is a 4-input OR/NOR gate. The device is functionally equivalent to the EL01 device, LVEL01, and E101 (a quad version). With AC performance much faster than the LVEL01 device, the EP01 is ideal for applications requiring the fastest AC performance available.

The 100 Series contains temperature compensation.

Features

- 230 ps Typical Propagation Delay
- Maximum Frequency = > 3 GHz Typical
- PECL Mode Operating Range: V_{CC} = 3.0 V to 5.5 V with V_{EE} = 0 V
- NECL Mode Operating Range: V_{CC} = 0 V with V_{EE} = -3.0 V to -5.5 V
- Open Input Default State
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

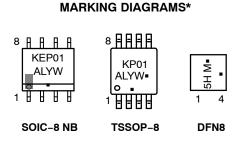


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SOIC-8 NBTSSOP-8DFN8D SUFFIXDT SUFFIXMN SUFFIXCASE 751-07CASE 948R-02CASE 506AA



		Α	= Assembly Location
		L	= Wafer Lot
K	= MC100	Υ	= Year
5H	= MC10	W	= Work Week
М	= Date Code		= Pb-Free Package

(Note: Microdot may be in either location) *For additional marking information, refer to Application Note <u>AND8002/D</u>.

ORDERING INFORMATION

Device	Package	Shipping [†]
MC10EP01MNR4G	DFN8 (Pb-Free)	1000 / Tape & Reel
MC100EP01DG	SOIC-8 NB (Pb-Free)	98 Units / Tube
MC100EP01DTG	TSSOP-8 (Pb-Free)	100 Units / Tube

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

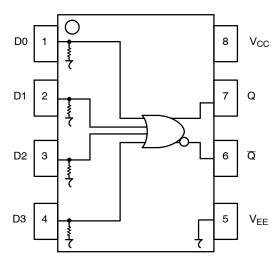


Figure 1. 8-Lead Pinout (Top View) and Logic Diagram

Table 1. PIN DESCRIPTION

Pin	Function
D0 – D3	ECL Data Inputs
Q, <u>Q</u>	ECL Data Outputs
V _{CC}	Positive Supply
V _{EE}	Negative Supply
EP	(DFN8 only) Thermal exposed pad must be connected to a sufficient thermal conduit. Elec- trically connect to the most negative supply (GND) or leave unconnected, floating open.

Table 2. TRUTH TABLE

D0*	D1*	D2*	D3*	q	Q
L	L	L	L	L	Н
Н	Х	Х	Х	Н	L
Х	Н	Х	Х	Н	L
Х	Х	Н	Х	Н	L
Х	Х	Х	Н	Н	L
Н	H	H	H	H	L

*Pins will default LOW when left open.

Table 3. ATTRIBUTES

Characteristics	Value
Internal Input Pulldown Resistor	75 kΩ
Internal Input Pullup Resistor	N/A
ESD Protection Human Body Model Machine Model Charged Device Model	> 4 kV > 200 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC–8 NB TSSOP–8 DFN8	Level 1 Level 3 Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V–0 @ 0.125 in
Transistor Count	115 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	

1. For additional information, see Application Note <u>AND8003/D</u>.

Table 4. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V _{CC}	PECL Mode Power Supply	V _{EE} = 0 V		6	V
V_EE	NECL Mode Power Supply	V _{CC} = 0 V		-6	V
VI	PECL Mode Input Voltage NECL Mode Input Voltage	V _{EE} = 0 V V _{CC} = 0 V	$\begin{array}{l} V_{I} \leq V_{CC} \\ V_{I} \geq V_{EE} \end{array}$	6 -6	V
l _{out}	Output Current	Continuous Surge		50 100	mA
I_{BB}	V _{BB} Sink/Source			±0.5	mA
T _A	Operating Temperature Range			-40 to +85	°C
T _{stg}	Storage Temperature Range			-65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 NB SOIC-8 NB	190 130	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8 NB	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP-8 TSSOP-8	185 140	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	DFN8 DFN8	129 84	°C/W
T _{sol}	Wave Solder (Pb-Free)	< 2 to 3 sec @ 260°C		265	°C
θJC	Thermal Resistance (Junction-to-Case)	(Note 2)	DFN8	35 to 40	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. JEDEC standard multilayer board - 2S2P (2 signal, 2 power)

–40°C 25°C 85°C Symbol Characteristic Min Тур Max Min Тур Max Min Тур Max Unit IEE Power Supply Current 20 24 31 20 24 31 20 24 31 mΑ Output HIGH Voltage (Note 2) 2165 2290 2415 2230 2355 2480 2290 2415 2540 mV VOH Output LOW Voltage (Note 2) 1365 1490 1615 1430 1555 1680 1490 1615 1740 mV VOL Input HIGH Voltage (Single-Ended) 2090 2415 2155 2480 2215 2540 mV VIH VIL Input LOW Voltage (Single-Ended) 1365 1690 1430 1755 1490 1815 mV Input HIGH Current 150 150 150 μA Iн 0.5 ΙL Input LOW Current 0.5 0.5 μΑ

Table 5. 10EP DC CHARACTERISTICS, PECL (V_{CC} = 3.3 V, V_{EE} = 0 V (Note 1))

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.3 V to -2.2 V.

2. All loading with 50 Ω to V_{CC} – 2.0 V.

			-40°C			25°C		85°C			
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	20	24	31	20	24	31	20	24	31	mA
V _{OH}	Output HIGH Voltage (Note 2)	3865	3990	4115	3930	4055	4180	3990	4115	4240	mV
V _{OL}	Output LOW Voltage (Note 2)	3065	3190	3315	3130	3255	3380	3190	3315	3440	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	3790		4115	3855		4180	3915		4240	mV
V_{IL}	Input LOW Voltage (Single-Ended)	3065		3390	3130		3455	3190		3515	mV
I _{IH}	Input HIGH Current			150			150			150	μA
IIL	Input LOW Current	0.5			0.5			0.5			μΑ

Table 6. 10EP DC CHARACTERISTICS, PECL (V_{CC} = 5.0 V, V_{EE} = 0 V (Note 1))

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +2.0 V to -0.5 V.

2. All loading with 50 Ω to V_{CC} – 2.0 V.

Table 7. 10EP DC CHARACTERISTICS, NECL ($V_{CC} = 0 \text{ V}$; $V_{EE} = -5.5 \text{ V}$ to -3.0 V (Note 1))

			–40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	20	24	31	20	24	31	20	24	31	mA
VOH	Output HIGH Voltage (Note 2)	-1135	-1010	-885	-1070	-945	-820	-1010	-885	-760	mV
V _{OL}	Output LOW Voltage (Note 2)	-1935	-1810	-1685	-1870	-1745	-1620	-1810	-1685	-1560	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	-1210		-885	-1145		-820	-1085		-760	mV
VIL	Input LOW Voltage (Single-Ended)	-1935		-1610	-1870		-1545	-1810		-1485	mV
I _{IH}	Input HIGH Current			150			150			150	μA
Ι _{ΙL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V_{CC} .

2. All loading with 50 Ω to V_{CC} – 2.0 V.

Table 8. 100EP DC CHARACTERISTICS, PECL (V_{CC} = 3.3 V, V_{EE} = 0 V (Note 1))

			-40°C		25°C			85°C			
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	15	24	32	17	26	36	19	28	38	mA
V _{OH}	Output HIGH Voltage (Note 2)	2155	2280	2405	2155	2280	2405	2155	2280	2405	mV
V _{OL}	Output LOW Voltage (Note 2)	1355	1480	1605	1355	1480	1605	1355	1480	1605	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	2075		2420	2075		2420	2075		2420	mV
V _{IL}	Input LOW Voltage (Single-Ended)	1355		1675	1355		1675	1355		1675	mV
I _{IH}	Input HIGH Current			150			150			150	μΑ
IIL	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V_{CC}^{-} , V_{EE} can vary +0.3 V to –2.2 V.

2. All loading with 50 Ω to V_{CC} – 2.0 V.

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	15	24	32	17	26	36	19	28	38	mA
V _{OH}	Output HIGH Voltage (Note 2)	3855	3980	4105	3855	3980	4105	3855	3980	4105	mV
V _{OL}	Output LOW Voltage (Note 2)	3055	3180	3305	3055	3180	3305	3055	3180	3305	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	3775		4120	3775		4120	3775		4120	mV
V _{IL}	Input LOW Voltage (Single-Ended)	3055		3375	3055		3375	3055		3375	mV
Ι _{ΙΗ}	Input HIGH Current			150			150			150	μΑ
IIL	Input LOW Current	0.5			0.5			0.5			μA

Table 9. 100EP DC CHARACTERISTICS, PECL (V_{CC} = 5.0 V, V_{EE} = 0 V (Note 1))

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +2.0 V to -0.5 V.

2. All loading with 50 Ω to V_{CC} – 2.0 V.

Table 10. 100EP DC CHARACTERISTICS, NECL ($V_{CC} = 0 \text{ V}$; $V_{EE} = -5.5 \text{ V}$ to -3.0 V (Note 1))

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	15	24	32	17	26	36	19	28	38	mA
V _{OH}	Output HIGH Voltage (Note 2)	-1145	-1020	-895	-1145	-1020	-895	-1145	-1020	-895	mV
V _{OL}	Output LOW Voltage (Note 2)	-1945	-1820	-1695	-1945	-1820	-1695	-1945	-1820	-1695	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	-1225		-880	-1225		-880	-1225		-880	mV
V _{IL}	Input LOW Voltage (Single-Ended)	-1945		-1625	-1945		-1625	-1945		-1625	mV
I _{IH}	Input HIGH Current			150			150			150	μA
۱ _{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V_{CC}. 2. All loading with 50 Ω to V_{CC} – 2.0 V.

			−40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f _{max}	Maximum Frequency (See Figure 2. F _{max} /JITTER)		> 3			> 3			> 3		GHz
t _{PLH} , t _{PHL}	Propagation Delay D to Q, \overline{Q}	150	260	330	150	270	330	200	300	350	ps
^t JITTER	Cycle-to-Cycle Jitter (See Figure 2. F _{max} /JITTER)		0.2	< 1		0.2	< 1		0.2	< 1	ps
t _r t _f	Output Rise/Fall Times Q, \overline{Q} (20%–80%)	50	120	170	60	130	180	70	150	200	ps

Table 11. AC CHARACTERISTICS (V_{CC} = 3.0 V to 5.5 V; V_{EE} = 0 V or V_{CC} = 0 V; V_{EE} = -3.0 V to -5.5 V (Note 1))

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Measured using a 750 mV source, 50% duty cycle clock source. All loading with 50 Ω to V_{CC} – 2.0 V.

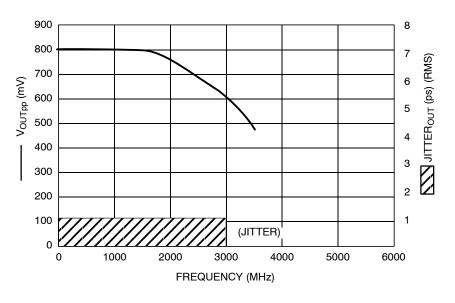


Figure 2. F_{max}/Jitter

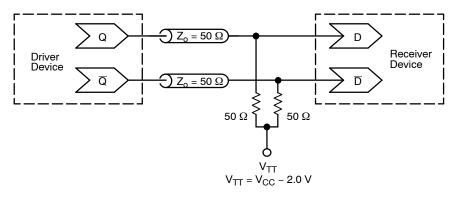


Figure 3. Typical Termination for Output Driver and Device Evaluation (See Application Note <u>AND8020/D</u> – Termination of ECL Logic Devices)

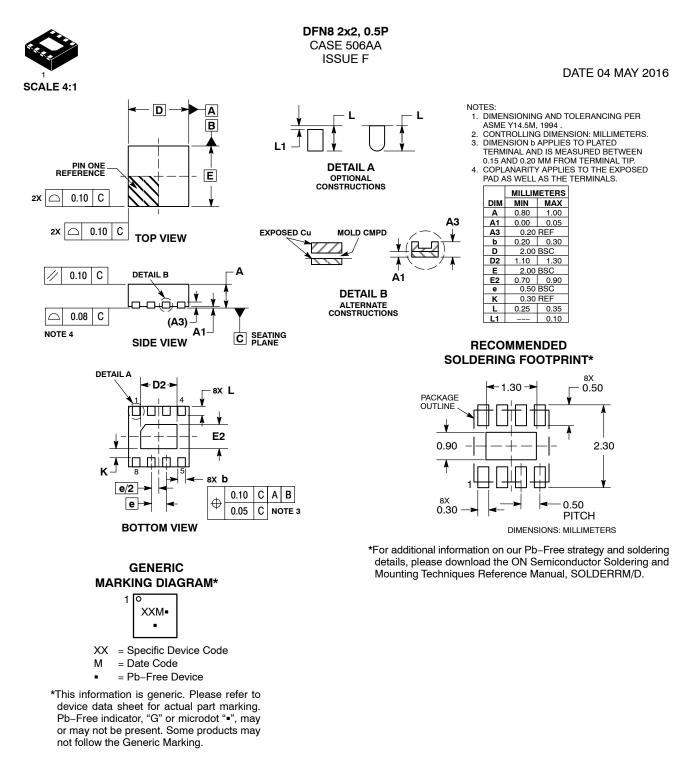
Resource Reference of Application Notes

AN1405/D	-	ECL Clock Distribution Techniques	
AN1406/D	-	Designing with PECL (ECL at +5.0 V)	
AN1503/D	-	ECLinPS [™] I/O SPiCE Modeling Kit	
AN1504/D	-	Metastability and the ECLinPS Family	
AN1568/D	-	Interfacing Between LVDS and ECL	
AN1672/D	-	The ECL Translator Guide	
AND8001/D	-	Odd Number Counters Design	
AND8002/D	-	Marking and Date Codes	
AND8020/D	-	Termination of ECL Logic Devices	

- AND8066/D Interfacing with ECLinPS
- AND8090/D AC Characteristics of ECL Devices

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*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE P-SOURCE 3 P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE 2. ANODE SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. 4. DRAIN, #2 GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. LINE 1 OUT 8. STYLE 27: PIN 1. ILIMIT 2 OVI 0 UVLO З. 4. INPUT+ 5. SOURCE SOURCE 6. SOURCE 7. 8 DRAIN

DATE 16 FEB 2011

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE, #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE 2. EMITTER 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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SOURCE 1/DRAIN 2

7.

8. GATE 1

COLLECTOR, #2

COLLECTOR, #1

COLLECTOR, #1

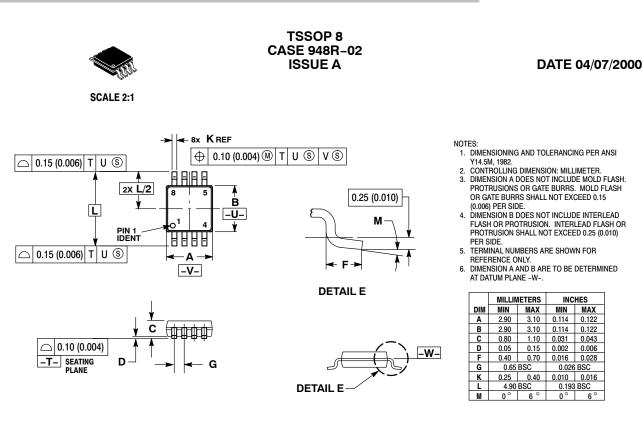
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